

High Speed Back-Illuminated InGaAs PIN Photodiode

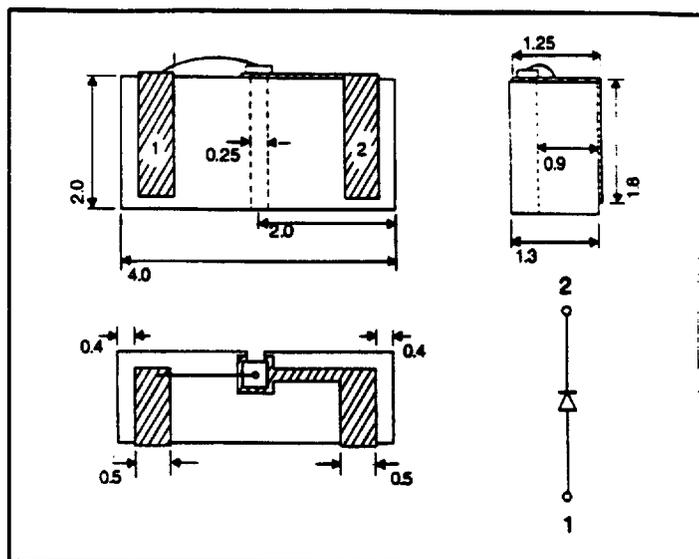
Description:

EPITAXX ETX 25B is a small area planar InGaAs photodiode mounted on a ceramic subcarrier. The device is illuminated through the substrate and its very low capacitance allows direct modulation at microwave frequencies.

Features:

- 25 μm active diameter
- grooved carrier
- optional custom submounts
- low dark current, low capacitance
- planar, passivated chip

Dimensions:



Maximum Ratings:

Parameter	Rating
Reverse Voltage	25V
Reverse Current	1mA
Forward Current	10mA
Operating Temperature	-40/ +85C
Storage Temperature	-40/ +100C

Optical/Electrical Characteristics (@ 25c)

Parameter	Conditions	Min	Typ	Max	Unit
Active Diameter			25		μm
Responsivity	$\lambda=1300\text{nm}$	0.70	0.80		A/W
Dark Current	$V_R=5\text{V}$		0.05		nA
Noise Current	$f=10\text{kHz}$		0.1		$\text{pA}/\sqrt{\text{Hz}}$
Total Capacitance	$V_R=5\text{V}$		0.1	0.2	pF
Bandwidth	$V_R=5\text{V}, 50\Omega, -3\text{dB}$		8000		MHz
Rise/Fall time	$V_R=5\text{V}, R_L=50\Omega$			0.05	nS

Corporate Headquarters

West Coast Sales Office

3490 US Route 1 • Princeton, NJ 08540
(609) 452-1188 • TLX: 759363 • FAX: (609) 452-0824

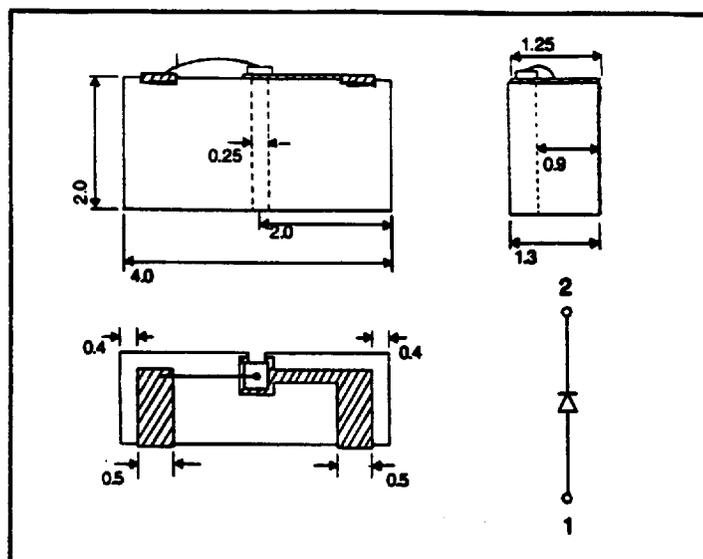
2121 Ave. of the Stars, 6 Fl • Los Angeles, CA 90067
(213) 551-6507 • FAX (213) 551-6577

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Dark Current	$V_R=5$ V		0.05		nA
Noise Current	$f=10$ kHz		0.1		$\text{pA}/\sqrt{\text{Hz}}$
Total Capacitance	$V_R=5$ V		0.1	0.2	pF
Bandwidth	$V_R=5$ V, $50\ \Omega$, -3dB	9000	10,000		MHz
Rise/Fall time	$V_R=5$ V, $R_L=50\ \Omega$			0.05	nS

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